

Features

- Low On-resistance, Ron=1.5Ω when VCC =5V
- 1.8V Logic Compatible Control Pin
- High Off-Isolation: -100dB @ 100KHz
- COM+/- Overrides VCC to Achieve True Isolation Even When Supply Is Dead
- Low Channel-to-Channel Crosstalk: -97dB @ 100KHz
- High Bandwidth (-3dB @550MHz) Suitable For USB2.0 High-Speed Routing
- Low Quiescent Current (<2uA) With Very Wide Supply Range (1.5V ~ 5.5V)

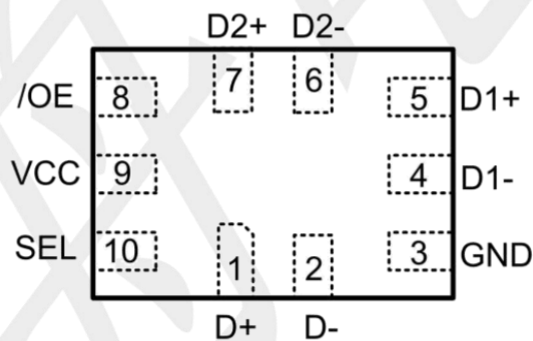
Applications

- Mobile Phones, Tablets and Notebooks
- Anywhere a USB Type-C™ or Micro-B Connector is Used

General Description

The is a bidirectional low-power dual port, high-speed, USB 2.0 analog switch with integrated protection for USB Type-C™ systems. The device is configured as a dual 2:1 or 1:2 switch. It is optimized for use with the USB 2.0 DP/DM lines in a USB Type-C™ system. The device is capable of true isolation. Even when COM+/- overrides VCC, very little current will flow back to the supply.has low bit-to-bit skew and high channel-to-channel noise isolation, and is compatible with various standards, such as high-speed USB 2.0 (480Mbps). Each switch is bidirectional and offers little or no attenuation of the high-speed signals at the outputs. Its bandwidth is wide enough to pass high-speed USB 2.0 differential signals (480 Mb/s) with good signal integrity.

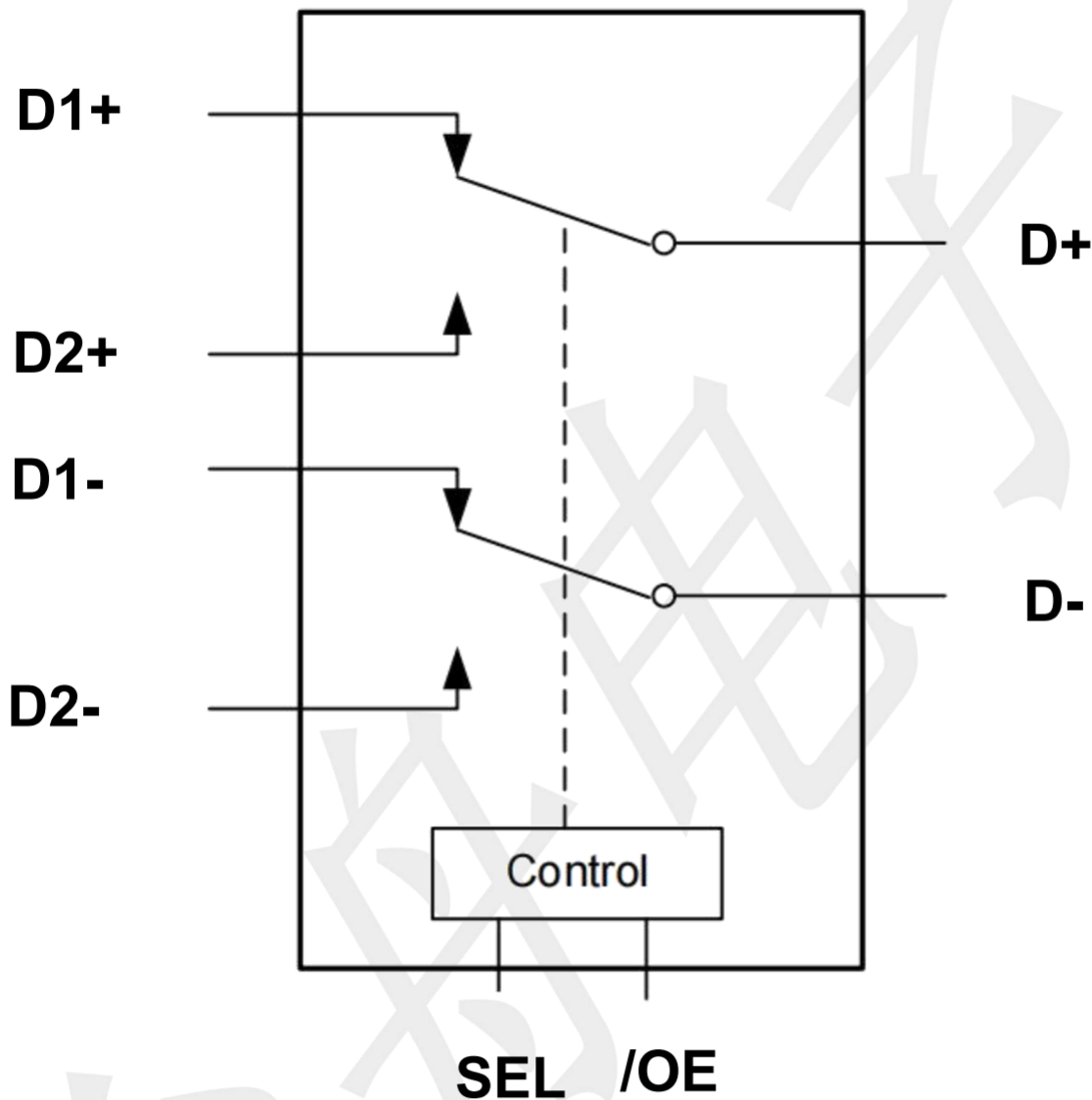
PIN CONFIGURATIONS (TOP VIEW)



PIN DESCRIPTION

PIN NO.	PIN NAME	DESCRIPTION
1	D+	Port A common data terminal, Connect to D1+ or D2+ according to SEL logic
2	D-	Port B common data terminal, Connect to D1- or D2- according to SEL logic
3	GND	Ground
4	D1-	Port B data 1 terminal
5	D1+	Port A data 1 terminal
6	D2-	Port B data 2 terminal
7	D2+	Port A data 2 terminal
8	/OE	Enable control, Active low
9	VCC	Power supply
10	SEL	Switch select pin, digital logic low or high

BLOCK DIAGRAM



Function Table

/OE	SEL	Function
H	X	Switch disconnected
L	L	D+ connect to D1+ and D- connect to D1-
L	H	D+ connect to D2+ and D- connect to D2-

Absolute Maximum Ratings

(Unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Supply Voltage	V _{CC}	-0.3 ~ +6.5	V
Input Voltage	V _{IN}	-0.3 ~ +6.5	V
Continuous Current Through D1, D2, D		±100	mA
Peak Current Through D1, D2, D (pulsed at 1ms 50% duty cycle)		±200	mA
Storage Temperature Range	T _{STG}	-55 ~ +150	°C
Operating Junction Temperature	T _J	150	°C
Lead Temperature (Soldering, 10 seconds)	T _L	260	°C
Power Dissipation	P _D	250	mW

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

Recommend operating ratings

(Unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Supply Voltage Operating	V _{CC}	1.5 ~ 5.5	V
Control Input Voltage	V _{IN}	-0.3 ~ 5.5	V
Input Signal Voltage	V _D	-0.3 ~ 5.5	V
Operating Temperature	T _A	-40 ~ +85	°C
Junction to Ambient	R _{θJA}	360	°C/W

DC Electrical Characteristics (TA =25°C, VC=+3.3V, unless otherwise specified)

PARAMETER	SYMBOL	TEST Conditions	MIN	TYP	MAX	UNIT
High-Level Input Voltage	V _{IH}	V _{CC} =3.3V ~ 5.5V	1.6	--	--	V
		V _{CC} =1.5V ~ 3.3V	1.4	--	--	V
Low-Level Input Voltage	V _{IL}	V _{CC} =3.3V ~ 5.5V	--	--	0.6	V
		V _{CC} =1.5V ~ 3.3V	--	--	0.4	V
Supply quiescent current	I _{CC}	I _A =0, V _{SEL} =0 or V _{SEL} =V _{CC}	--	--	1.0	uA
Increase in I _{CC} per input	I _{CC} T	I _A =0, V _{CC} =4.5V V _{SEL} >1.8 or V _{SEL} <0.5	--	--	1.0	uA
Off state leakage from COM _x to NC _x (or NO _x)	I _{COMx}	V _{COM} = 5.5V, V _{NC(or NO)} = 0V	--	--	±2.0	uA
On-Resistance	R _{ON1}	V _A =0 ~ 0.5V, I _A =30mA	--	3.6	3.9	Ω
	R _{ON2}	V _A =0.5 ~ 2.0V, I _A =30mA	--	3.0	3.5	Ω
	R _{ON3}	V _A =2.0 ~ 4.0V, I _A =30mA	--	2.5	3.5	Ω
	R _{ON4}	V _A =4.0 ~ 5.5V, I _A =30mA	--	1.5	1.8	Ω
On-Resistance Flatness	R _{FLAT1}	V _A =0 ~ 0.5V, I _A =30mA	--	1.6	--	Ω
	R _{FLAT2}	V _A =0.5 ~ 2.0V, I _A =30mA	--	0.7	--	Ω
	R _{FLAT3}	V _A =2.0 ~ 4.0V, I _A =30mA	--	0.5	--	Ω
	R _{FLAT4}	V _A =4.0 ~ 5.5V, I _A =30mA	--	0.3	--	Ω
On-Resistance Matching Between Channels	Δ R _{ON}	V _A =0~5.5V, I _A =30mA	--	0.1	0.2	Ω

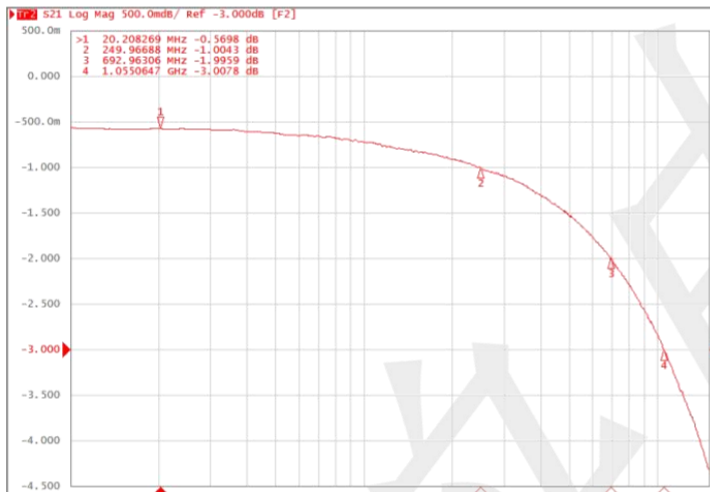
AC Electronics Characteristics (Ta=25°C, VCC=+3.3V, unless otherwise noted)

PARAMETER	SYMBOL	TEST Conditions	MIN	TYP	MAX	UNIT
Turn-On Time	T _{ON}	V _A =1.5V, C _L =35pF, R _L =50Ω	--	200	--	ns
Turn-Off Time	T _{OFF}	V _A =1.5V, C _L =35pF, R _L =50Ω	--	200	--	ns
Break-Before-Make time	T _B BM	V _A =1.5V, C _L =35pF, R _L =50Ω	--	500	--	ns
-3dB Bandwidth	BW	R _L =50Ω, C _L =5pF	--	550	--	MHz
		R _L =50Ω, C _L =0pF	--	800	--	MHz
Off isolation	OIRR	F=1KHz, R _L =50Ω	--	-81	--	dB
		F=10KHz, R _L =50Ω	--	-80	--	dB
Crosstalk	Xtalk	F=1KHz, R _L =50Ω	--	-83	--	dB
		F=10KHz, R _L =50Ω	--	-82	--	dB
Total Harmonic Distortion	THD	F=20Hz to 20KHz V _A =600mVp-p @R _L =32Ω	--	-80	--	dB

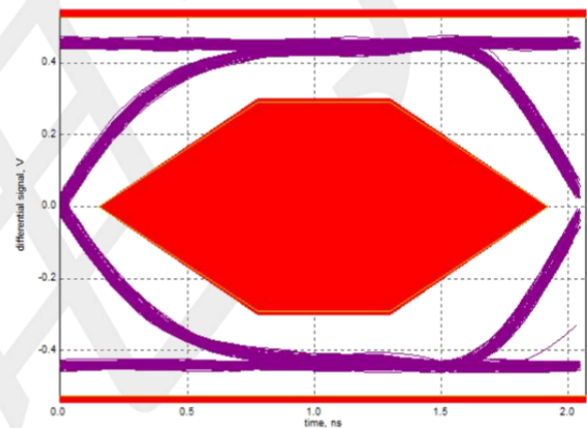
Capacitance (Ta=25°C, VCC=+3.3V, unless otherwise noted)

PARAMETER	SYMBOL	TEST Conditions	MIN	TYP	MAX	UNIT
Off capacitance	C _{OFF}	F=100KHZ,	--	5.0	--	pF
On capacitance	C _{ON}	F=100KHZ,	--	7.0	--	pF

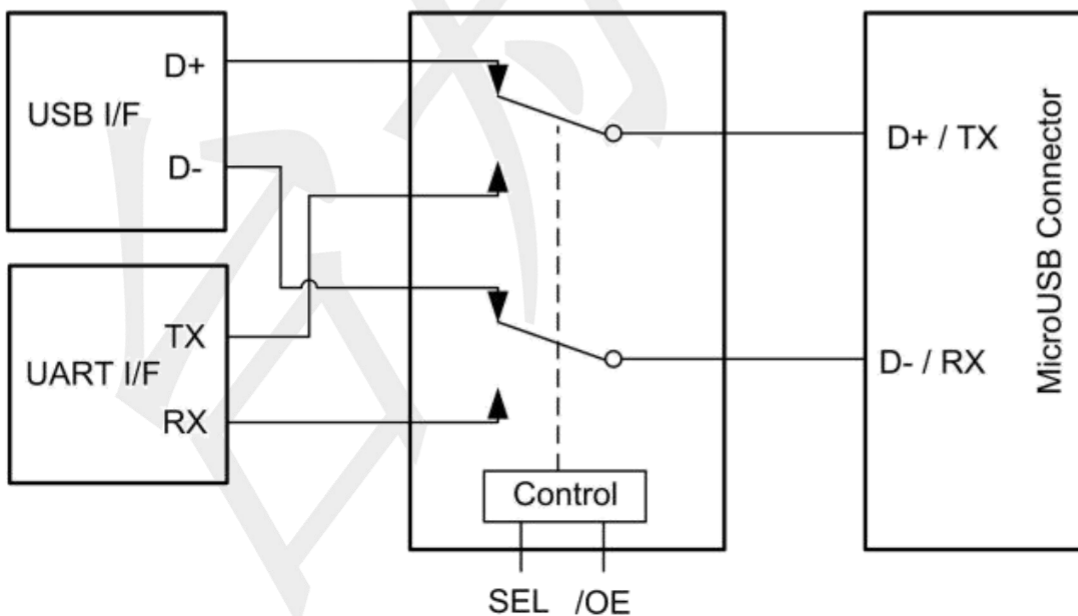
Typical Characteristics (Ta=25oC, VCC=3.3V, unless otherwise noted)



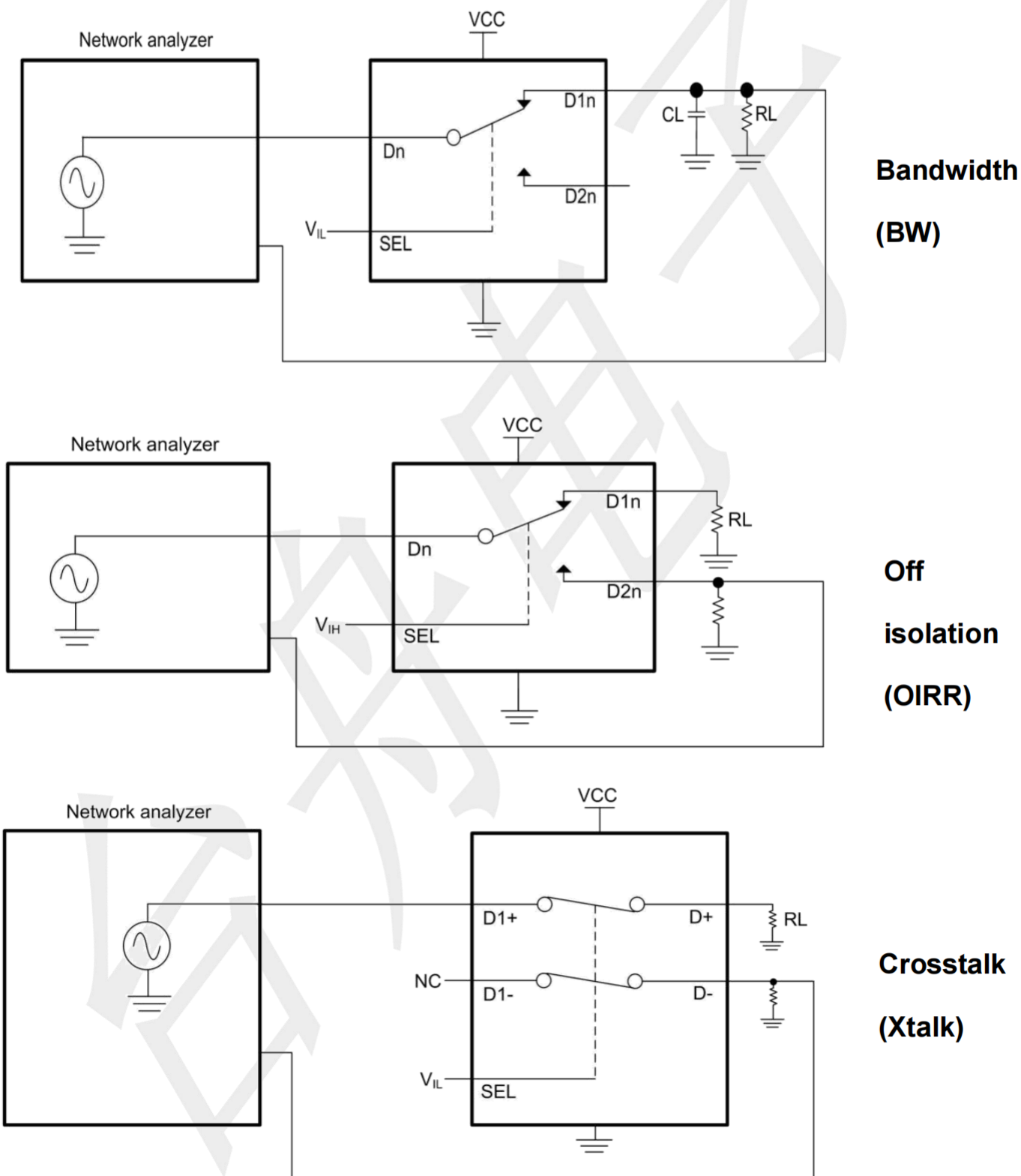
Bandwidth



Eye Diagram (480Mbps)

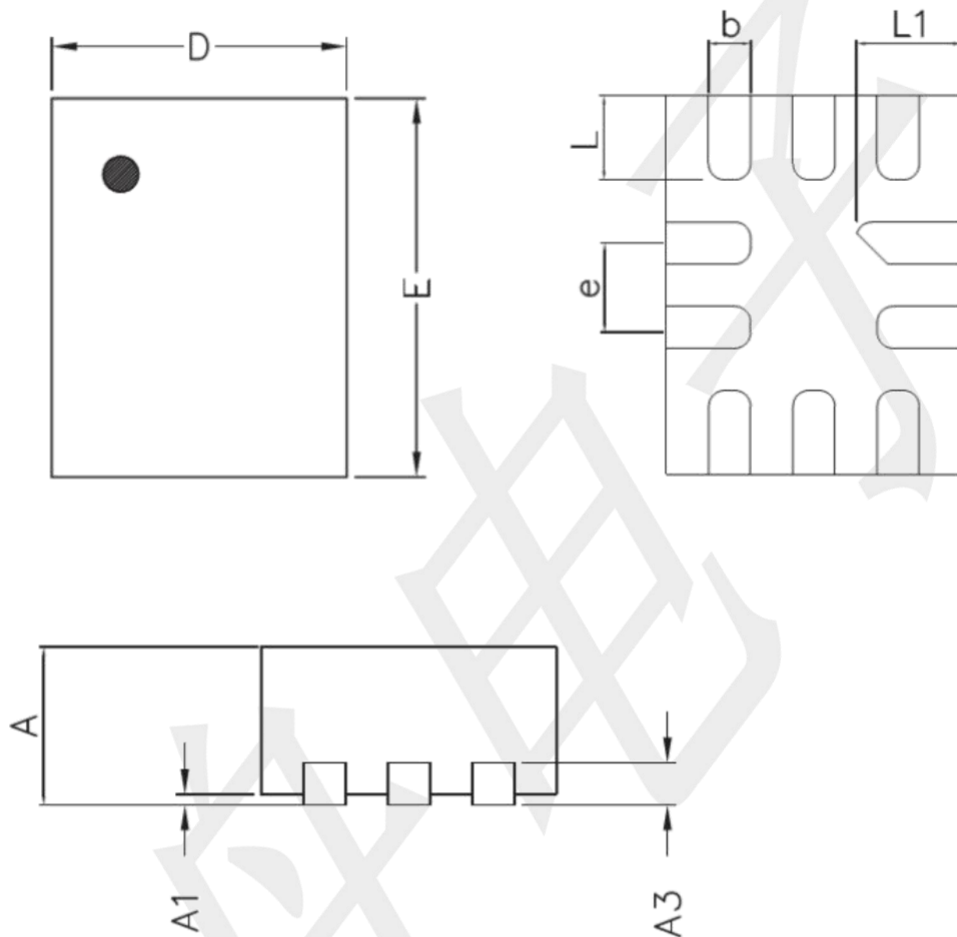


Typical Characteristics (Ta=25oC, VCC=3.3V, unless otherwise noted)



Package information

QFN1418-10L (Unit: mm)



Symbol	Dimension in Millimeters	
	Min.	Max.
A	0.450	0.550
A1	0.000	0.050
A3	0.152 Ref.	
D	1.350	1.450
E	1.750	1.850
b	0.150	0.250
e	0.400 Typ.	
L	0.350	0.450
L1	0.450	0.550